

DOSEMI

IGBT

DG75Q12T2

1200V/75A IGBT with Diode

General Description

DOSEMI IGBT Power Discrete provides ultra low conduction loss as well as low switching loss. They are designed for the applications such as general inverters and UPS.

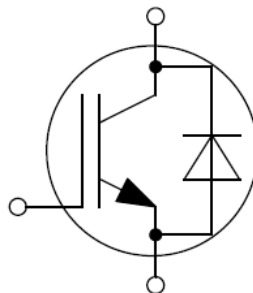
Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- Low switching loss
- Maximum junction temperature 175°C
- $V_{CE(sat)}$ with positive temperature coefficient
- Fast & soft reverse recovery anti-parallel FWD
- Lead free package

Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Values	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	150	A
	@ $T_C=134^{\circ}\text{C}$	75	
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	225	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	937	W

Diode

Symbol	Description	Values	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	75	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	225	A

Discrete

Symbol	Description	Values	Unit
T_{jop}	Operating Junction Temperature	-40 to +175	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-55 to +150	$^{\circ}\text{C}$
T_S	Soldering Temperature, 1.6mm from case for 10s	260	$^{\circ}\text{C}$

IGBT Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=75\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		1.90	2.35	V	
		$I_C=75\text{A}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}$		2.30			
		$I_C=75\text{A}, V_{GE}=15\text{V}, T_j=175^\circ\text{C}$		2.40			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=3.0\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.6	6.2	6.8	V	
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			350	μA	
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			100	nA	
R_{Gint}	Internal Gate Resistance			5.0		Ω	
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=100\text{kHz}, V_{GE}=0\text{V}$		7.46		nF	
C_{res}	Reverse Transfer Capacitance				0.18		nF
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		0.57		μC	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=75\text{A}, R_G=6.8\Omega, V_{GE}=\pm 15\text{V}, L_S=40\text{nH}, T_j=25^\circ\text{C}$		91		ns	
t_r	Rise Time			158		ns	
$t_{d(off)}$	Turn-Off Delay Time			299		ns	
t_f	Fall Time			136		ns	
E_{on}	Turn-On Switching Loss			13.1		mJ	
E_{off}	Turn-Off Switching Loss			2.56		mJ	
$t_{d(on)}$	Turn-On Delay Time		$V_{CC}=600\text{V}, I_C=75\text{A}, R_G=6.8\Omega, V_{GE}=\pm 15\text{V}, L_S=40\text{nH}, T_j=150^\circ\text{C}$		93		ns
t_r	Rise Time				168		ns
$t_{d(off)}$	Turn-Off Delay Time			306		ns	
t_f	Fall Time			201		ns	
E_{on}	Turn-On Switching Loss			15.9		mJ	
E_{off}	Turn-Off Switching Loss			3.20		mJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=75\text{A}, R_G=6.8\Omega, V_{GE}=\pm 15\text{V}, L_S=40\text{nH}, T_j=175^\circ\text{C}$			94		ns
t_r	Rise Time				169		ns
$t_{d(off)}$	Turn-Off Delay Time			313		ns	
t_f	Fall Time			211		ns	
E_{on}	Turn-On Switching Loss			16.9		mJ	
E_{off}	Turn-Off Switching Loss			3.45		mJ	
I_{SC}	SC Data		$t_P \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$		300		A

Diode Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=75\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.85	2.30	V
		$I_F=75\text{A}, V_{GE}=0\text{V}, T_j=150^\circ\text{C}$		1.95		
		$I_F=75\text{A}, V_{GE}=0\text{V}, T_j=175^\circ\text{C}$		2.00		
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=75\text{A},$ $-di/dt=290\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $L_S=40\text{nH}, T_j=25^\circ\text{C}$		3.46		μC
I_{RM}	Peak Reverse Recovery Current			20.3		A
E_{rec}	Reverse Recovery Energy			1.79		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=75\text{A},$ $-di/dt=310\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $L_S=40\text{nH}, T_j=150^\circ\text{C}$		3.51		μC
I_{RM}	Peak Reverse Recovery Current			24.6		A
E_{rec}	Reverse Recovery Energy			3.33		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=75\text{A},$ $-di/dt=350\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $L_S=40\text{nH}, T_j=175^\circ\text{C}$		3.87		μC
I_{RM}	Peak Reverse Recovery Current			25.7		A
E_{rec}	Reverse Recovery Energy			3.73		mJ

Discrete Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
R_{thJC}	Junction-to-Case (per IGBT)			0.160	K/W
	Junction-to-Case (per Diode)			0.260	
R_{thJA}	Junction-to-Ambient		40		K/W

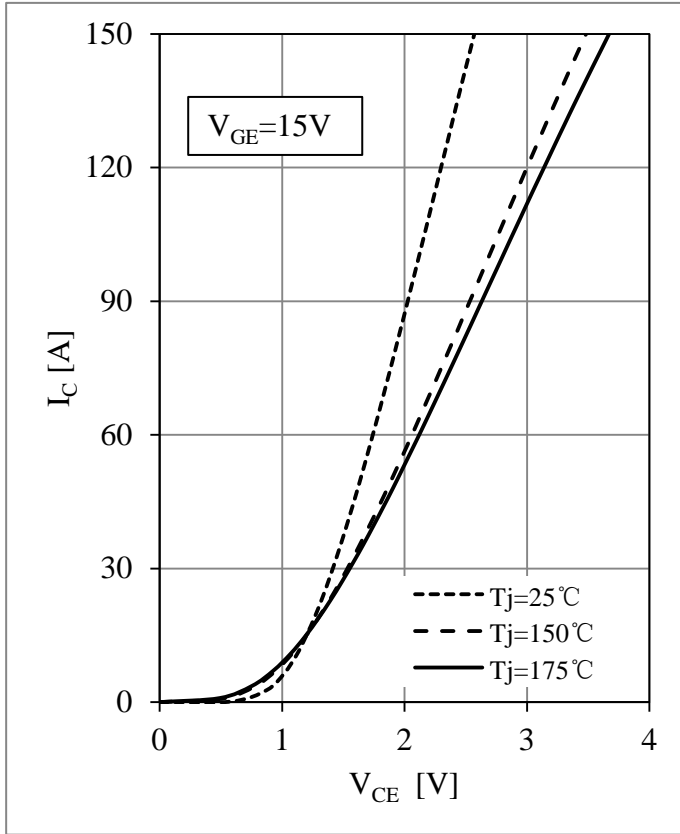


Fig 1. IGBT-inverter Output Characteristics

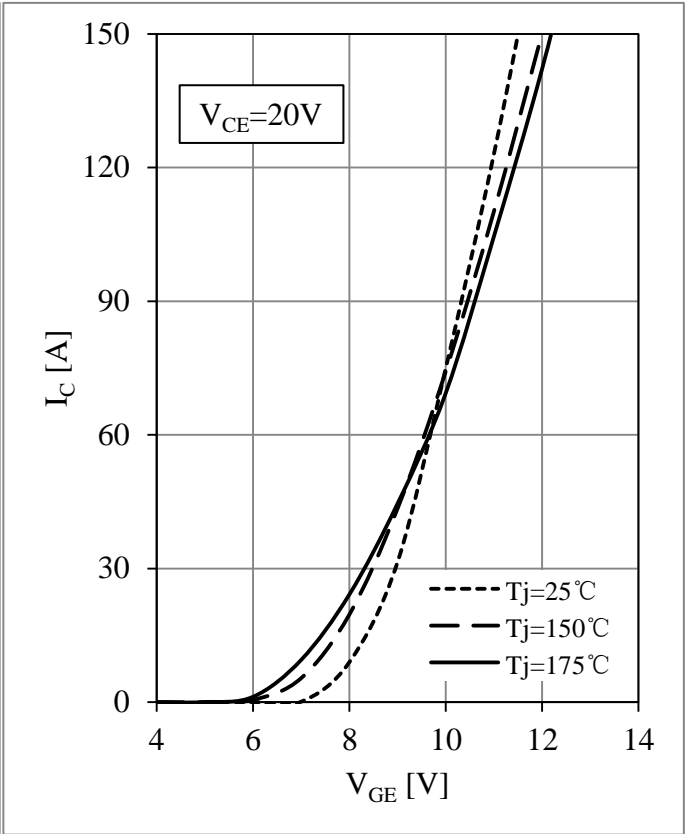


Fig 2. IGBT-inverter Transfer Characteristics

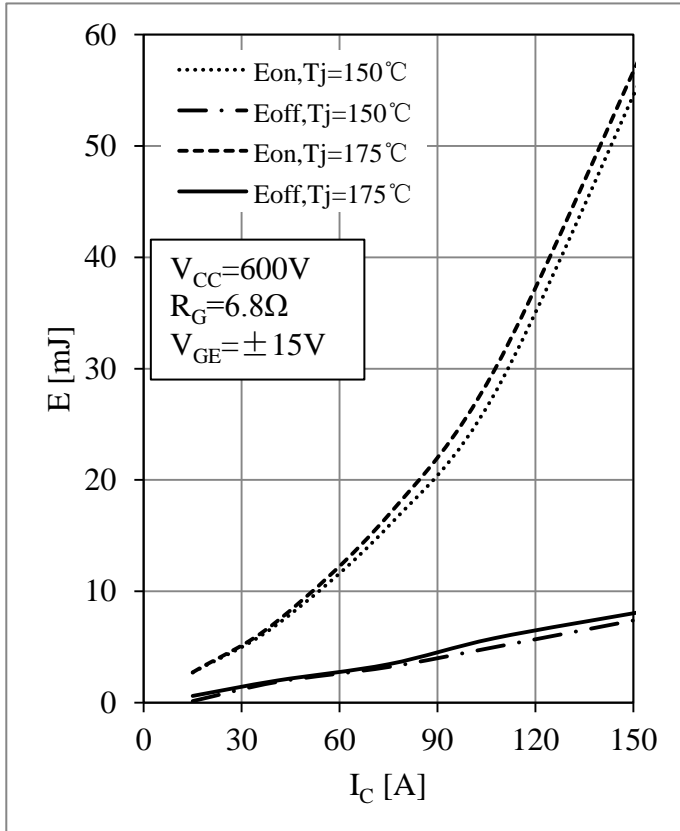


Fig 3. IGBT-inverter Switching Loss vs. I_C

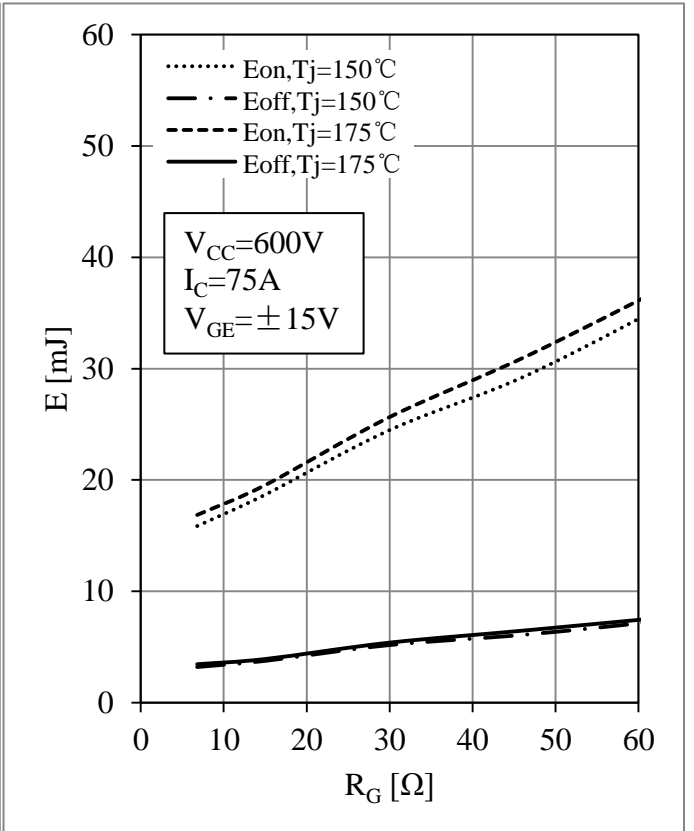


Fig 4. IGBT-inverter Switching Loss vs. R_G

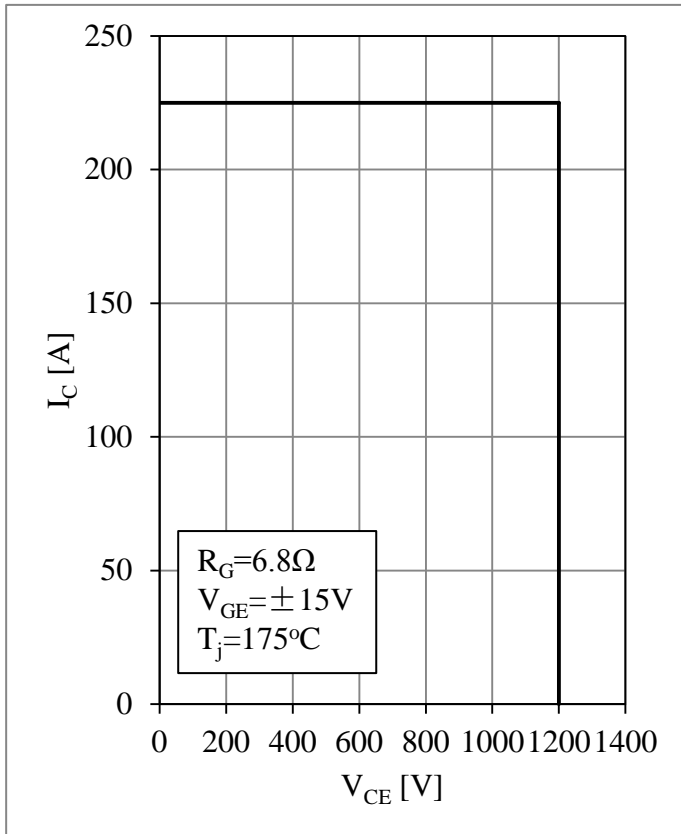


Fig 5. IGBT-inverter RBSOA

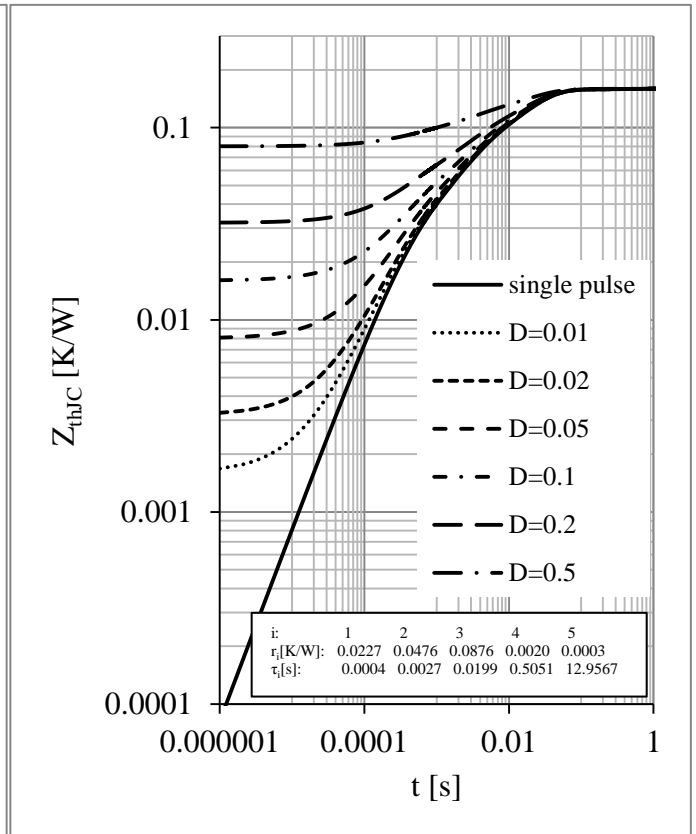


Fig 6. IGBT-inverter Transient Thermal Impedance

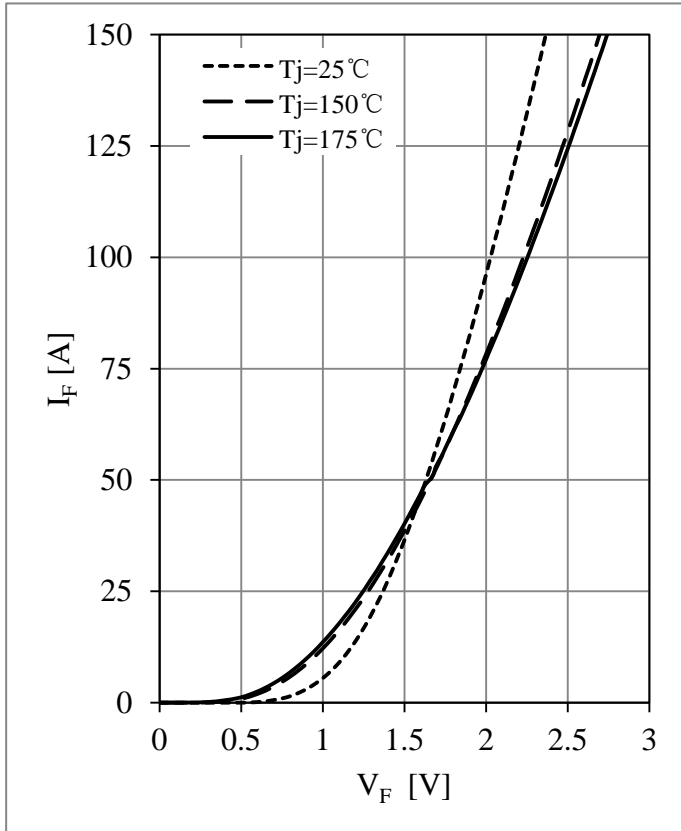


Fig 7. Diode-inverter Forward Characteristics

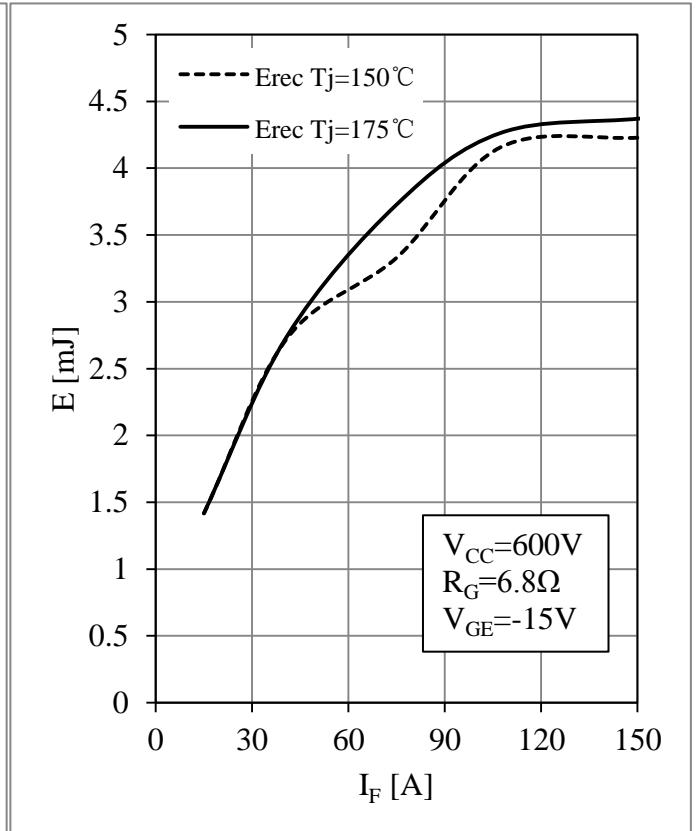


Fig 8. Diode-inverter Switching Loss vs. I_F

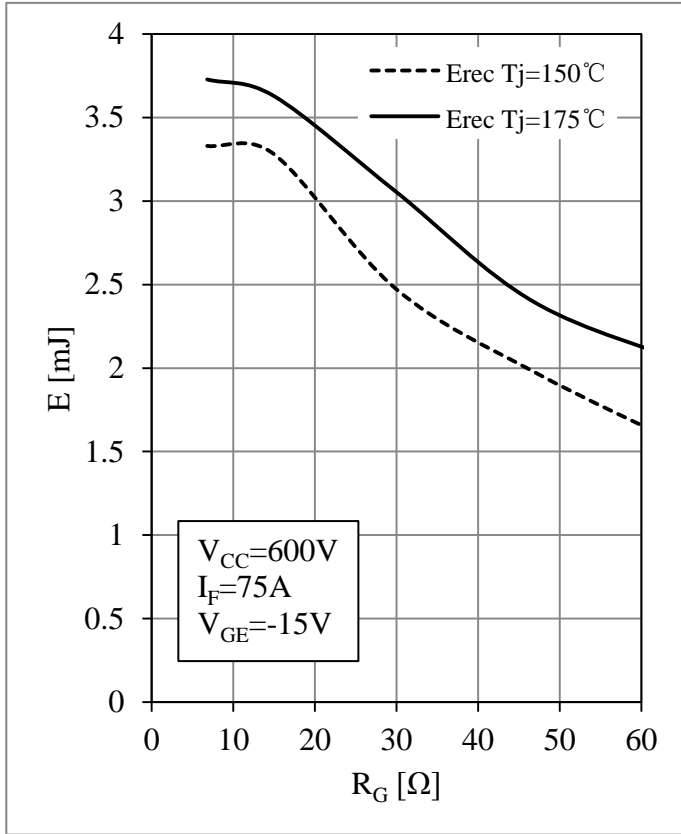


Fig 9. Diode-inverter Switching Loss vs. R_G

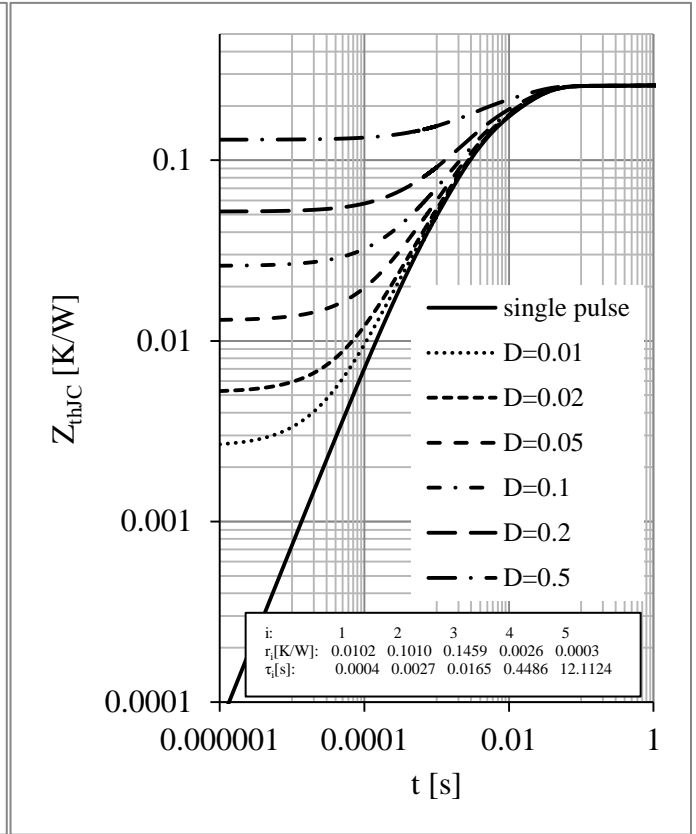
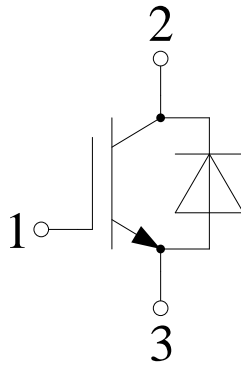


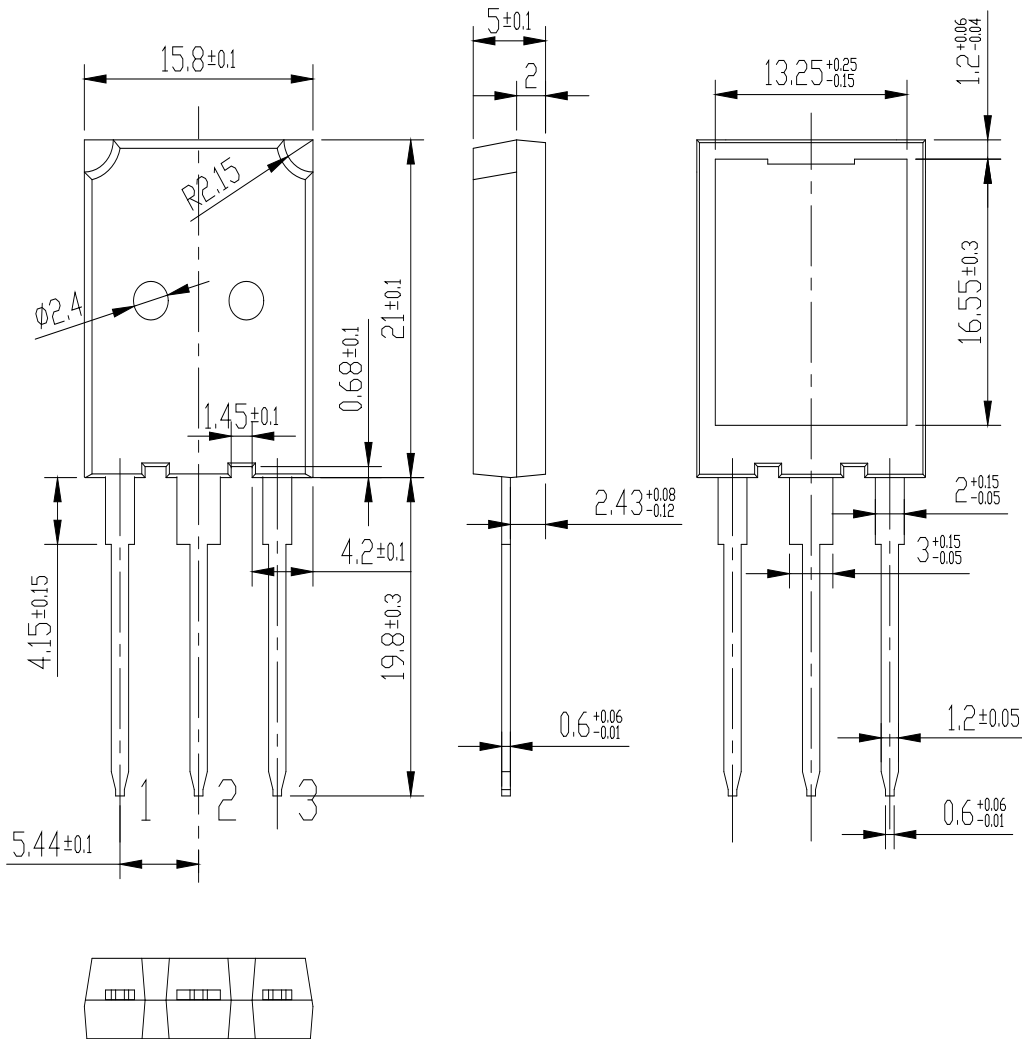
Fig 10. Diode-inverter Transient Thermal Impedance

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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